# NPIC6C596-Q100

Power logic 8-bit shift register; open-drain outputs

Rev. 3 — 22 June 2020

Product data sheet

# 1. General description

The NPIC6C596-Q100 is an 8-bit serial-in/serial or parallel-out shift register with a storage register and open-drain outputs. Both the shift and storage register have separate clocks. The device features a serial input (DS) and a serial output (Q7S) to enable cascading and an asynchronous reset  $\overline{\text{MR}}$  input. A LOW on  $\overline{\text{MR}}$  resets both the shift register and storage register. Data is shifted on the LOW-to-HIGH transitions of the SHCP input. The data in the shift register is transferred to the storage register on a LOW-to-HIGH transition of the STCP input. If both clocks are connected together, the shift register is always one clock pulse ahead of the storage register. To provide additional hold time in cascaded applications, the serial output QS7 is clocked out on the falling edge of SHCP. Data in the storage register drives the gate of the output extended-drain NMOS (EDNMOS) transistor whenever the output enable input ( $\overline{\text{OE}}$ ) is LOW. A HIGH on  $\overline{\text{OE}}$  causes the outputs to assume a high-impedance OFF-state. Operation of the  $\overline{\text{OE}}$  input does not affect the state of the registers.

The open-drain outputs are 33 V/100 mA continuous current extended-drain NMOS transistors designed for use in systems that require moderate load power such as LEDs. Integrated voltage clamps in the outputs provide protection against inductive transients making the device suitable for power driver applications such as relays, solenoids and other low-current or medium-voltage loads.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from -40 °C to +125 °C
- Low R<sub>DSon</sub>
- Eight Power EDNMOS transistor outputs of 100 mA continuous current
- 250 mA current limit capability
- Output clamping voltage 33 V
- 30 mJ avalanche energy capability
- Enhanced cascading for multiple stages
- All registers cleared with single input
- Low power consumption
- ESD protection:
  - HBM AEC-Q100-002 revision D exceeds 2500 V
  - CDM AEC-Q100-011 revision B exceeds 1000 V
- DHVQFN package with Side-Wettable Flanks enabling Automatic Optical Inspection (AOI) of solder joints

# 3. Applications

- LED sign
- Graphic status panel
- · Fault status indicator

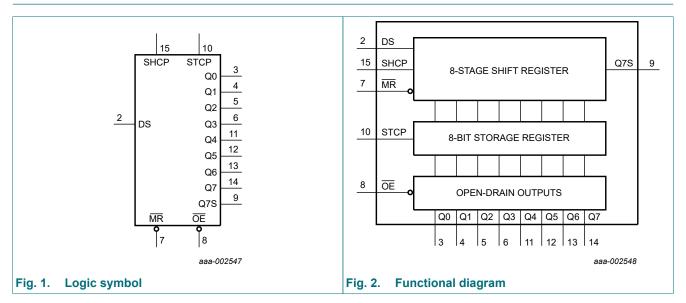


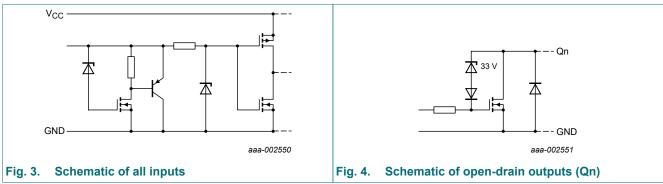
# 4. Ordering information

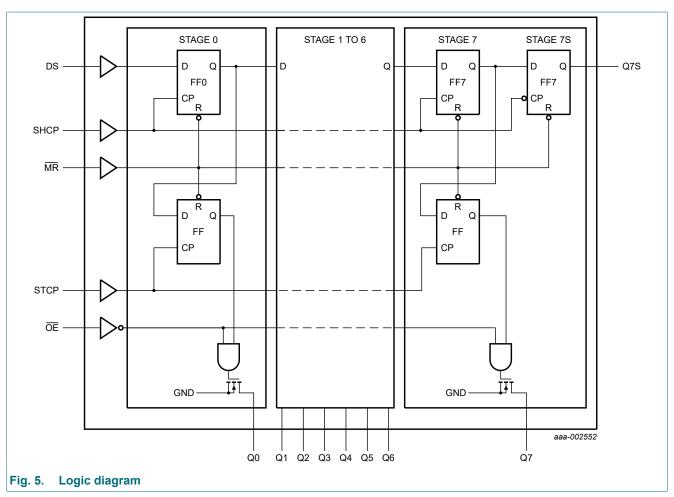
**Table 1. Ordering information** 

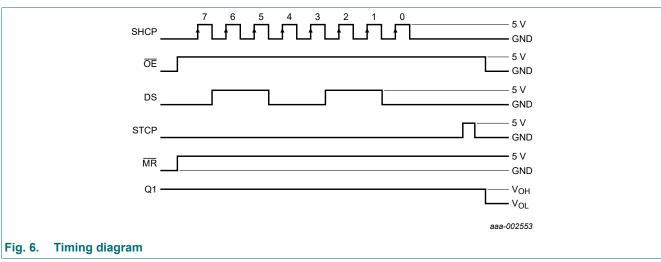
Type number	Package					
	Temperature range	Name	Description	Version		
NPIC6C596D-Q100	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1		
NPIC6C596PW-Q100	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1		
NPIC6C596BQ-Q100	-40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1		

# 5. Functional diagram







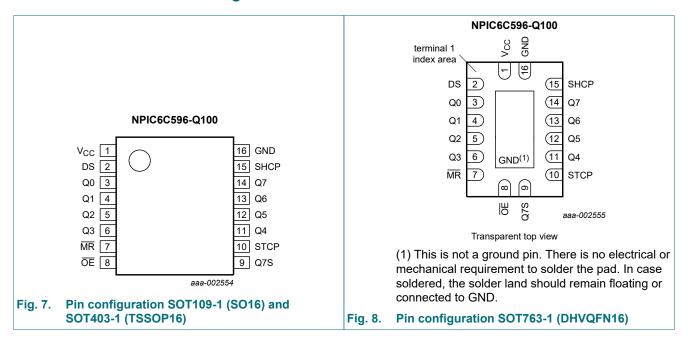


**Product data sheet** 

3 / 18

# 6. Pinning information

## 6.1. Pinning



## 6.2. Pin description

Table 2. Pin description

Symbol	Pin	Description
V <sub>CC</sub>	1	supply voltage
DS	2	serial data input
Q0, Q1, Q2, Q3, Q4, Q5, Q6, Q7	3, 4, 5, 6, 11, 12, 13, 14	parallel data output (open-drain)
MR	7	master reset (active LOW)
ŌE	8	output enable input (active LOW)
Q7S	9	serial data output
STCP	10	storage register clock input
SHCP	15	shift register clock input
GND	16	ground (0 V)

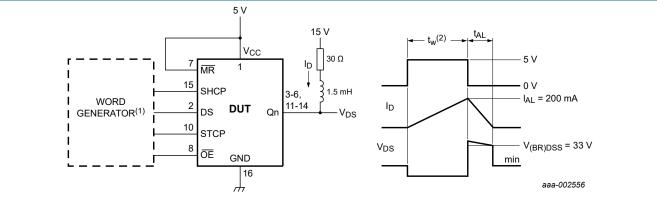
# 7. Limiting values

#### **Table 3. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+7.0	V
VI	input voltage			-0.3	+7.0	V
V <sub>DS</sub>	drain-source voltage	power EDNMOS drain-source voltage	[1]	-	+33	V
I <sub>d(SD)</sub>	source-drain diode current	continuous		-	250	mA
		pulsed	[2]	-	500	mA
I <sub>D</sub>	drain current	T <sub>amb</sub> = 25 °C				
		continuous; each output; all outputs on		-	100	mA
		pulsed; each output; all outputs on	[2]	-	250	mA
I <sub>DM</sub>	peak drain current	single output; T <sub>amb</sub> = 25 °C	[2]	-	250	mA
E <sub>AS</sub>	avalanche energy	single pulse; see Fig. 9	[3]	-	30	mJ
I <sub>AL</sub>	avalanche current	see Fig. 9	[3]	-	200	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[4]			
		SOT109-1 (SO16)		-	800	mW
		SOT403-1 (TSSOP16)		-	725	mW
		SOT763-1 (DHVQFN16)		-	1825	mW
		T <sub>amb</sub> = 125 °C	[4]			
		SOT109-1 (SO16)		-	160	mW
		SOT403-1 (TSSOP16)		-	145	mW
		SOT763-1 (DHVQFN16)		-	365	mW

- [1] Each power EDNMOS source is internally connected to GND.
- [2] Pulse duration ≤ 100 µs and duty cycle ≤ 2 %.
- [3]  $V_{DS} = 15 \text{ V}$ ; starting junction temperature ( $T_j$ ) = 25 °C; L = 1.5 H; avalanche current ( $I_{AL}$ ) = 200 mA.
- [4] For SO16 packages: above 25 °C the value of P<sub>tot</sub> derates linearly with 6.4 mW/°C. For TSSOP16 packages: above 25 °C the value of P<sub>tot</sub> derates linearly with 5.8 mW/°C.
  - For DHVQFN16 packages: above 25 °C the value of Ptot derates linearly with 14.6 mW/°C.



- (1) The word generator has the following characteristics:  $t_r$ ,  $t_f \le 10$  ns;  $Z_0 = 50 \Omega$ .
- (2) The input pulse duration ( $t_W$ ) is increased until peak current  $I_{AL}$  = 200 mA. Energy test level is defined as:  $E_{AS} = I_{AL} \times V_{(BR)DSS} \times t_{AL}/2 = 30$  mJ.
- Fig. 9. Test circuit and waveform for measuring single-pulse avalanche energy

# 8. Recommended operating conditions

#### Table 4. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		4.5	-	5.5	V
VI	input voltage		0	-	5.5	V
I <sub>D</sub>	drain current	pulsed drain output current; $V_{CC} = 5 \text{ V}$ ; [1] [2] $T_{amb} = 25 \text{ °C}$ ; all outputs on	-	-	250	mA
T <sub>amb</sub>	ambient temperature		-40	-	+125	°C

<sup>[1]</sup> Pulse duration ≤ 100 µs and duty cycle ≤ 2 %.

# 9. Static characteristics

### **Table 5. Static characteristics**

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	V <sub>CC</sub> = 5.	0 V; T <sub>aml</sub>	<sub>o</sub> = 25 °C	Unit
			Min	Тур	Max	
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	0.85V <sub>CC</sub>	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	0.15V <sub>CC</sub>	V
V <sub>OH</sub>	· ·	serial data output Q7S; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
	voltage	I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.49	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 4.5 V	4.0	4.2	-	V
$V_{OL}$	LOW-level output	serial data output Q7S; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
	voltage	I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0.005	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 4.5 V	-	0.3	0.5	V
I <sub>IH</sub>	HIGH-level input current	$V_{CC} = 5.5 \text{ V}; V_{I} = V_{CC}$		-	1	μΑ
I <sub>IL</sub>	LOW-level input current	$V_{CC} = 5.5 \text{ V}; V_I = 0 \text{ V}$		-	-	μΑ
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 1 mA	33	37	-	V
$V_{SD}$	source-drain voltage	diode forward voltage; I <sub>F</sub> = 100 mA	-	0.85	1.2	V
I <sub>CC</sub>	supply current	logic supply current; $V_{CC} = 5.5 \text{ V}$ ; $V_I = V_{CC}$ or GND				
		all outputs off	-	0.004	200	μA
		all outputs on [1]	-	0.006	500	μA
		all outputs off; SHCP = 5 MHz; C <sub>L</sub> = 30 pF; see Fig. 14 and Fig. 16	-	0.75	5	mA
I <sub>O(nom)</sub>	nominal output current	$V_{DS} = 0.5 \text{ V}; T_{amb} = 85 \text{ °C}; I_{out} = I_{D}$ [2] [3] [4]		140	-	mA
I <sub>DSX</sub>	drain cut-off	V <sub>CC</sub> = 5.5 V; V <sub>DS</sub> = 30 V	-	0.002	0.2	μA
	current	V <sub>CC</sub> = 5.5 V; V <sub>DS</sub> = 30 V; T <sub>amb</sub> = 125 °C	-	0.15	0.3	μA

<sup>[2]</sup> Technique should limit T<sub>j</sub> - T<sub>amb</sub> to 10 °C maximum.

Symbol	Parameter	Conditions V <sub>CC</sub> = 5.0 V; T <sub>amb</sub>		Γ <sub>amb</sub> = 25 °C		
			Min	Тур	Max	
R <sub>DSon</sub>	drain-source on-	see Fig. 17 and Fig. 18 [2] [3]				
	state resistance	$V_{CC} = 4.5 \text{ V}; I_D = 50 \text{ mA}$	-	3.0	9	Ω
		$V_{CC}$ = 4.5 V; $I_{D}$ = 50 mA; $T_{amb}$ = 125 °C		5.4	12	Ω
		V <sub>CC</sub> = 4.5 V; I <sub>D</sub> = 100 mA	-	3.1	10	Ω

- Output currents below 250 mA current limit.
- Technique should limit T<sub>i</sub> T<sub>amb</sub> to 10 °C maximum.
- These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts. [3]
- Nominal output current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at  $T_{amb}$  = 85 °C.

# 10. Dynamic characteristics

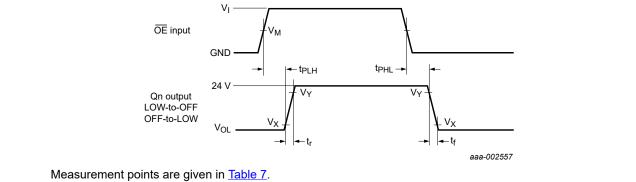
### **Table 6. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); For test circuit see Fig. 14.

Symbol	Parameter	Conditions		V <sub>CC</sub> = 5	Unit		
				Min	Тур	Max	
t <sub>PLH</sub>	LOW to HIGH propagation delay	OE to Qn; I <sub>D</sub> = 75 mA; see <u>Fig. 10</u> and <u>Fig. 19</u>		-	97	-	ns
t <sub>PHL</sub>	HIGH to LOW propagation delay	OE to Qn; I <sub>D</sub> = 75 mA; see <u>Fig. 10</u> and <u>Fig. 19</u>		-	9	-	ns
t <sub>r</sub>	rise time	OE to Qn; I <sub>D</sub> = 75 mA; see <u>Fig. 10</u> and <u>Fig. 19</u>	, 5		60	-	ns
t <sub>f</sub>	fall time	OE to Qn; I <sub>D</sub> = 75 mA; see <u>Fig. 10</u> and <u>Fig. 19</u>		-	18	-	ns
t <sub>pd</sub>	propagation delay	SHCP to Q7S; I <sub>D</sub> = 75 mA; see Fig. 11	[1]	-	5	-	ns
f <sub>max</sub>	maximum frequency	SHCP; I <sub>D</sub> = 75 mA; see <u>Fig. 11</u>	[2]	-	-	10	MHz
t <sub>rr</sub>	reverse recovery time	$I_F = 100 \text{ mA}$ ; dI/dt = 10 A/ $\mu$ s; see Fig. 13	[3] [4]	-	120	-	ns
t <sub>a</sub>	reverse recovery current rise time	$I_F = 100 \text{ mA}$ ; dI/dt = 10 A/ $\mu$ s; see Fig. 13	[3] [4]	-	100	-	ns
t <sub>su</sub>	set-up time	DS to SHCP; see Fig. 12		15	-	-	ns
t <sub>h</sub>	hold time	DS to SHCP; see Fig. 12		15	-	-	ns
t <sub>W</sub>	pulse width			40	-	-	ns

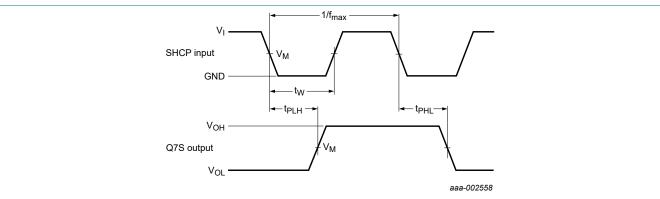
- $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ . This is the maximum serial clock frequency assuming cascaded operation where serial data is passed from one stage to a second stage. The clock period allows for SHCP  $\overset{\checkmark}{ o}$  Q7S propagation delay and setup time plus some timing margin.
- Technique should limit T<sub>i</sub> T<sub>amb</sub> to 10 °C maximum.
- These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

### 10.1. Test circuits and waveforms



V<sub>OL</sub> is the typical output voltage level that occurs with the output load.

Fig. 10. The output enable (OE) input to data output (Qn) propagation delays and (Qn) output rise and fall times



Measurement points are given in Table 7.

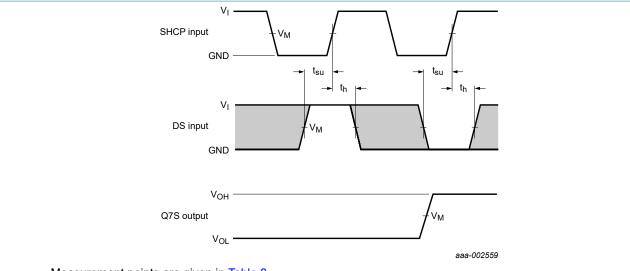
V<sub>OL</sub> and V<sub>OH</sub> are the typical output voltage levels that occur with the output load.

Fig. 11. The shift clock (SHCP) to serial data output (Q7S) propagation delays with the minimum shift clock pulse width and maximum shift clock frequency

**Table 7. Measurement points** 

Supply voltage	Input	Output		
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
5 V	0.5V <sub>CC</sub>	0.5V <sub>DS</sub>	0.1V <sub>DS</sub>	0.9V <sub>DS</sub>

8 / 18



Measurement points are given in Table 8.

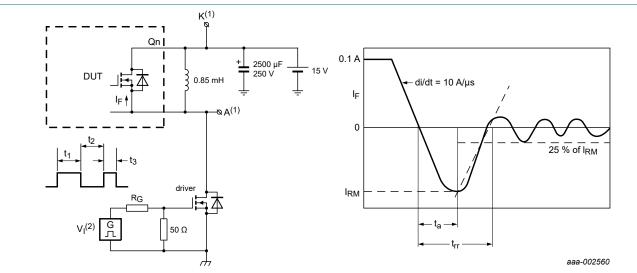
The shaded areas indicate when the input is permitted to change for predictable output performance.

 $V_{\text{OL}}$  and  $V_{\text{OH}}$  are the typical output voltage levels that occur with the output load.

Fig. 12. The data set-up and hold times for the serial data input (DS)

**Table 8. Measurement points** 

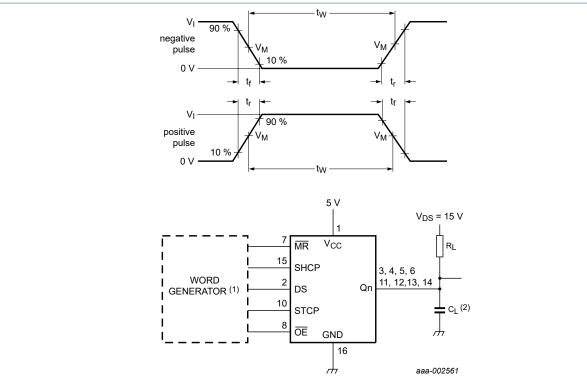
Supply voltage	Input	Output
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>
5 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>



- (1) The open-drain Qn terminal under test is connected to test point K. All other terminals are connected together and connected to test point A.
- (2) The  $V_I$  amplitude and  $R_G$  are adjusted for dI/dt = 10 A/ $\mu$ s. A  $V_I$  double-pulse train is used to set  $I_F$  = 0.1 A, where  $t_1$  = 10  $\mu$ s,  $t_2$  = 7  $\mu$ s and  $t_3$  = 3  $\mu$ s.

Fig. 13. Test circuit and waveform for measuring reverse recovery current

Product data sheet



- (1) The word generator has the following characteristics:  $t_r$ ,  $t_f \le 10$  ns;  $t_W = 300$  ns; pulsed repetition rate (PRR) = 5 kHz;  $Z_O = 50 \Omega$ .
- (2) C<sub>L</sub> includes probe and jig capacitance.

Test data is given in <u>Table 9</u>. Definitions for test circuit:

V<sub>DS</sub> = External voltage for Power EDNMOS drain-source voltage.

R<sub>L</sub> = Load resistance.

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

Fig. 14. Test circuit for measuring switching times

Table 9. Test data

Supp	oly voltage	Input			Load	
		V <sub>I</sub>	t <sub>r</sub> , t <sub>f</sub>	V <sub>M</sub>	CL	$R_L$
5 V		5 V	≤ 10 ns	50 %	30 pF	200 Ω

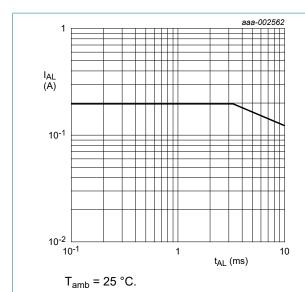


Fig. 15. Avalanche current (peak) versus time duration of avalanche

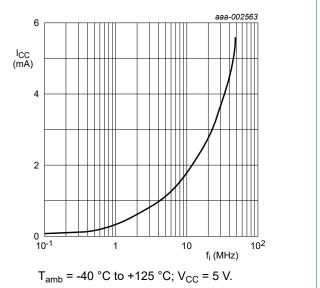
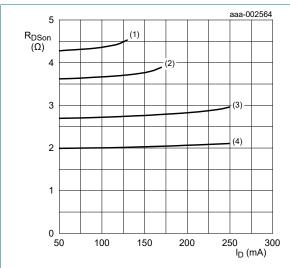


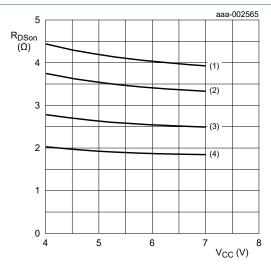
Fig. 16. Supply current versus frequency



 $V_I = V_{CC}$  or GND and  $V_O = GND$  or  $V_{CC}$ .

- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2) T<sub>amb</sub> = 85 °C
- (3)  $T_{amb}$  = 25 °C
- (4)  $T_{amb}$  = -40 °C

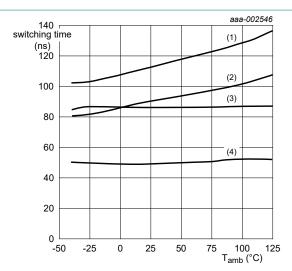
Fig. 17. Drain-source on-state resistance versus drain current



 $V_I = V_{CC}$  or GND and  $V_O =$  open circuit.

- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2) T<sub>amb</sub> = 85 °C
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig. 18. Static drain-source on-state resistance versus supply voltage



Technique limit  $T_J$  -  $T_C$  to 10 °C maximum.

- (1) t<sub>PLH</sub>.
- (2) t<sub>r</sub>.
- $(3) t_f$
- (4) t<sub>PHL</sub>.

Fig. 19. Switching time versus case temperature

12 / 18

# 11. Package outline

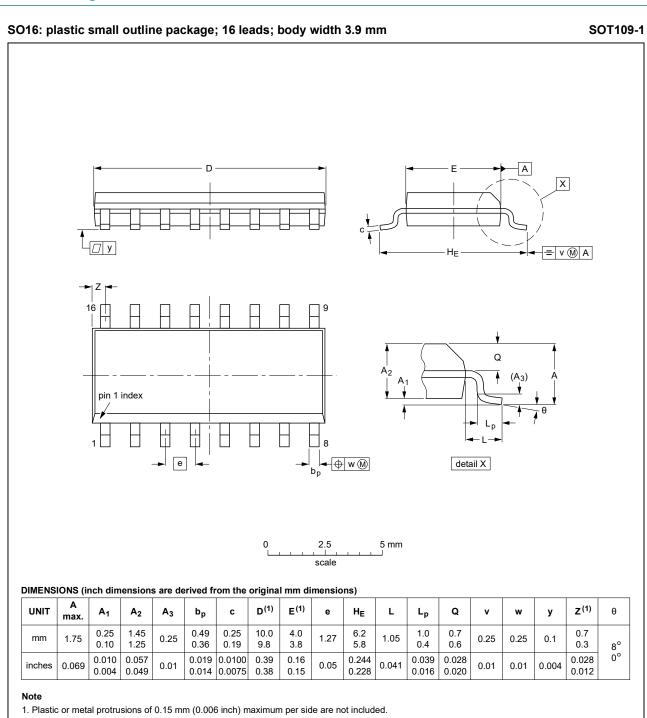


Fig. 20. Package outline SOT109-1 (SO16)

IEC

076E07

OUTLINE

VERSION

SOT109-1

**JEITA** 

**REFERENCES** 

**JEDEC** 

MS-012

**ISSUE DATE** 

99-12-27

03-02-19

**EUROPEAN** 

PROJECTION

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

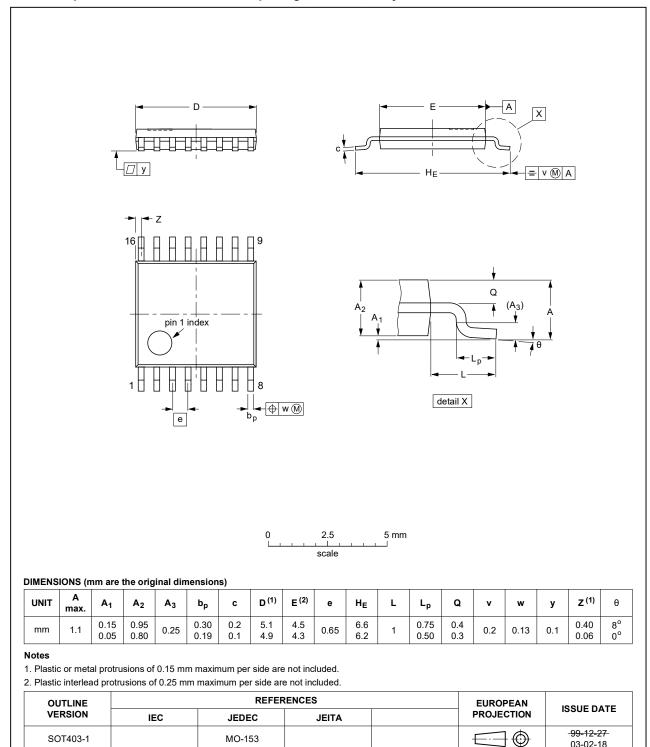


Fig. 21. Package outline SOT403-1 (TSSOP16)

MO-153

SOT403-1

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

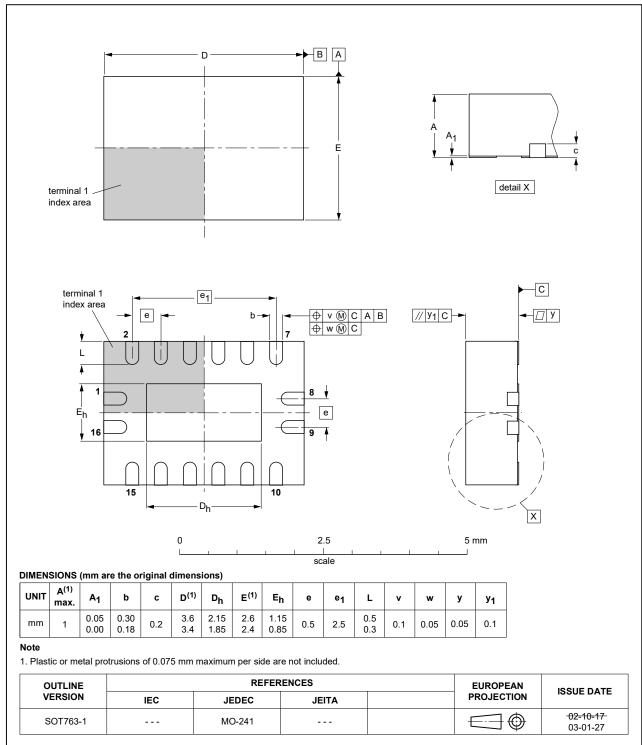


Fig. 22. Package outline SOT763-1 (DHVQFN16)

**Product data sheet** 

# 12. Abbreviations

### **Table 10. Abbreviations**

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
EDNMOS	Extended Drain Negative Metal Oxide Semiconductor
ESD	ElectroStatic Discharge
НВМ	Human Body Model

# 13. Revision history

#### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
NPIC6C596_Q100 v.3	20200622	Product data sheet	-	NPIC6C596_Q100 v.2			
Modifications:	guidelines • Legal texts	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Section 2 updated.</li> </ul>					
NPIC6C596_Q100 v.2	20130704	Product data sheet	-	NPIC6C596_Q100 v.1			
Modifications:	• Fig. 5 corre	• Fig. 5 corrected (errata).					
NPIC6C596_Q100 v.1	20120712	Product data sheet	-	-			

# 14. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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#### Power logic 8-bit shift register; open-drain outputs

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# **Contents**

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Ordering information	2
5. Functional diagram	2
6. Pinning information	4
6.1. Pinning	4
6.2. Pin description	4
7. Limiting values	5
8. Recommended operating conditions	6
9. Static characteristics	6
10. Dynamic characteristics	7
10.1. Test circuits and waveforms	8
11. Package outline	13
12. Abbreviations	
13. Revision history	16
14. Legal information	17

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